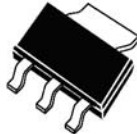


CZT122 NPN
CZT127 PNP

COMPLEMENTARY SILICON
POWER DARLINGTON TRANSISTOR

POWER
223TM



SOT-223 CASE

CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CZT122, CZT127 types are Complementary Silicon Power Darlington Transistors manufactured in a surface mount package designed for low speed switching and amplifier applications.

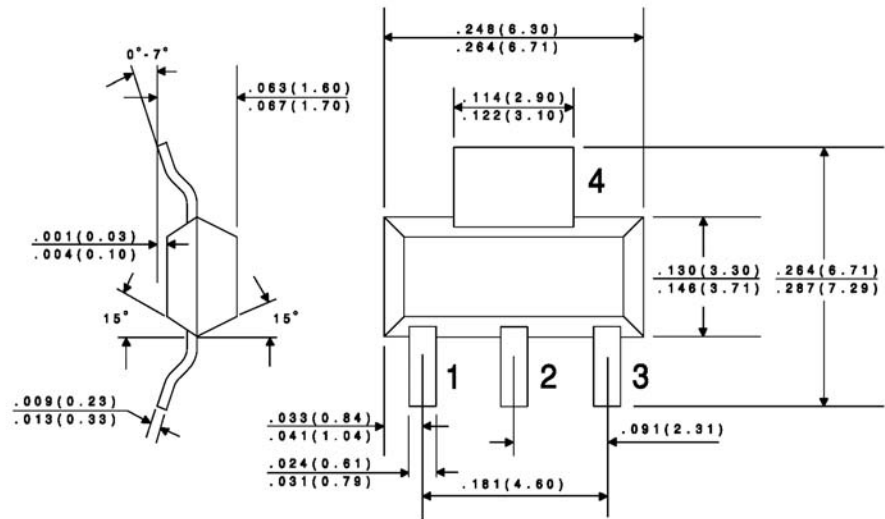
MAXIMUM RATINGS: (T_A=25°C)

	SYMBOL		UNITS
Collector-Base Voltage	V _{CBO}	100	V
Collector-Emitter Voltage	V _{CEO}	100	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Collector Current	I _C	5.0	A
Peak Collector Current	I _{CM}	8.0	A
Base Current	I _B	120	mA
Power Dissipation	P _D	2.0	W
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JA}	62.5	°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{CEO}	V _{CE} =50V		500	μA
I _{CBO}	V _{CB} =100V		200	μA
I _{EBO}	V _{EB} =5.0V		2.0	mA
BV _{CEO}	I _C =30mA	100		V
V _{CE(SAT)}	I _C =3.0A, I _B =12mA		2.0	V
V _{CE(SAT)}	I _C =5.0A, I _B =20mA		4.0	V
V _{BE(ON)}	V _{CE} =3.0V, I _C =3.0A		2.5	V
h _{FE}	V _{CE} =3.0V, I _C =500mA	1000		
h _{FE}	V _{CE} =3.0V, I _C =3.0A	1000		
f _T	V _{CE} =4.0V, I _C =3.0A, f=1.0MHz	4.0		MHz
C _{ob}	V _{CB} =10V, I _E =0, f=1.0MHz (CZT122)		200	pF
C _{ob}	V _{CB} =10V, I _E =0, f=1.0MHz (CZT127)		300	pF

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 4) COLLECTOR